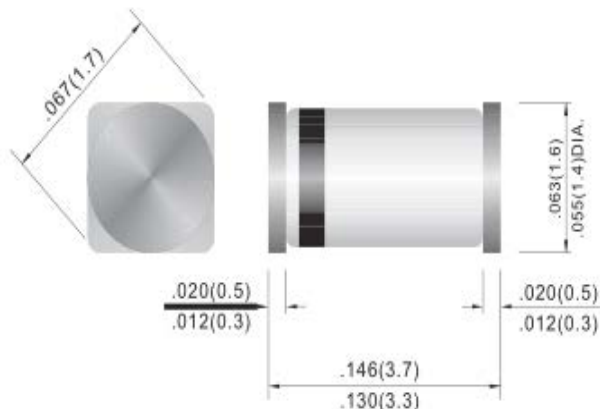


Fast Switching Diodes

REVERSE VOLTAGE - 75 Volts
FORWARD CURRENT - 0.2 Amperes

FEATURES

- Fast switching diode in MiniMELF case especially suited for automatic surface mounting

DL-35


Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

MAXIMUM RATINGS

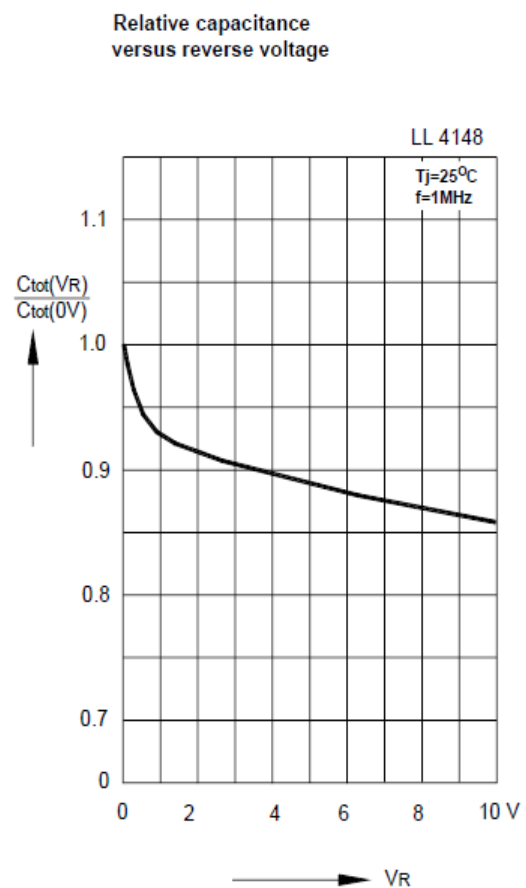
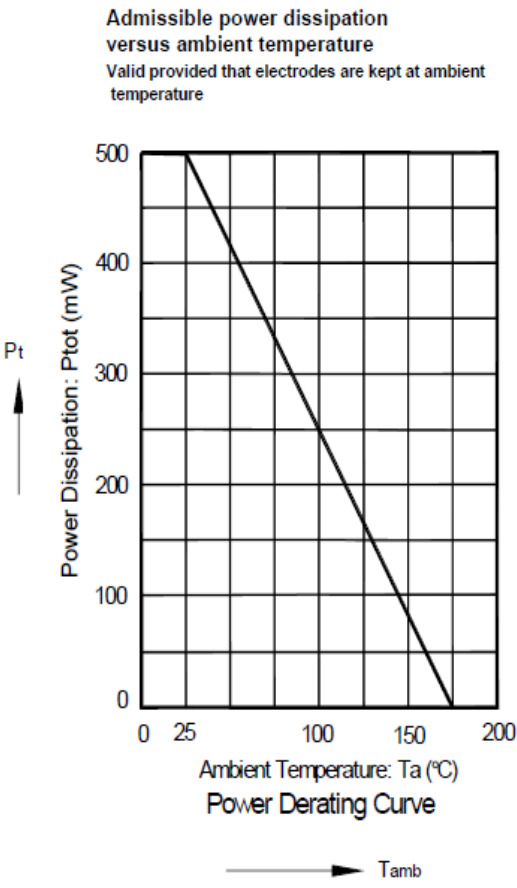
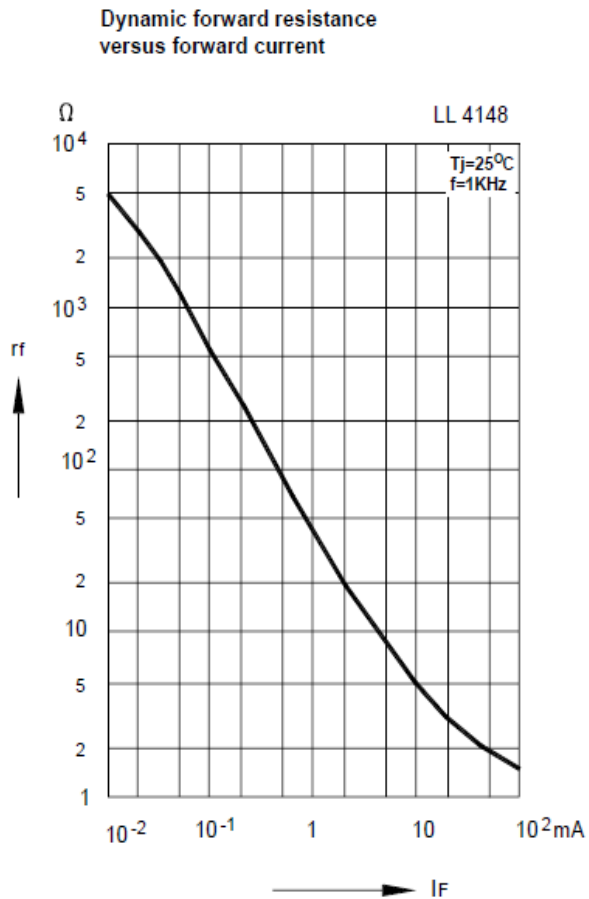
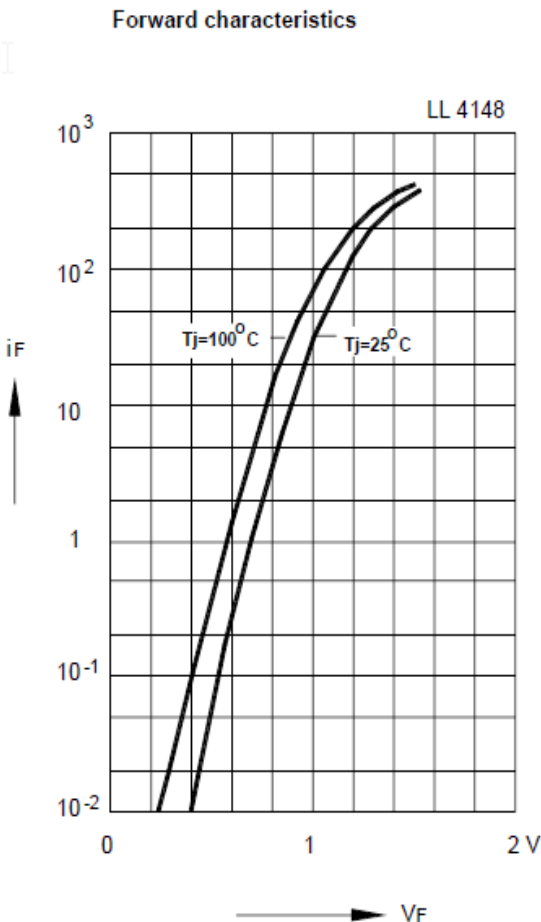
CHARACTERISTICS	SYMBOL	LL4148	UNIT
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5	A
at $t = 1$ s		1	
at $t = 1$ ms		4	
Power Dissipation	P_{tot}	500 ⁽¹⁾	mW
Junction Temperature	T_J	-55 to + 150	°C
Storage Temperature Range	T_{STG}	-65 to + 175	°C

NOTE:(1) Valid provided that electrodes are kept at ambient temperature .

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MIN	MAX	UNIT
Reverse Breakdown Voltage tested with 100 μ A Pulses	$V_{(BR)R}$	100	-	V
Forward Voltage at $I_F=10$ mA	V_F	-	1	V
Leakage Current	I_R	-	25	nA
at $V_R=20$ V				uA
at $V_R=75$ V				uA
at $V_R=20$ V $T_J=150^\circ$ C	I_R	-	50	uA
Capacitance at $V_R=0$ V, $f=1$ MHZ	C_{tot}	-	4	pF
Voltage Rise When Switching ON Tested With 50mA Pulses $t_p=0.1\mu$ s. Rise Time<30ns. $f_p=5$ to 100Hz	V_{fr}	-	2.5	v
Reverse Recovery Time From $I_F=10$ mA $V_R=6$ V. $R_L=100\Omega$ at $I_R=1$ mA	t_{rr}	-	4	ns
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	-	350 ⁽¹⁾	°C/W
Rectification Efficiency at 100MHZ $V_{RF}=2$ V	η V	0.45	-	-

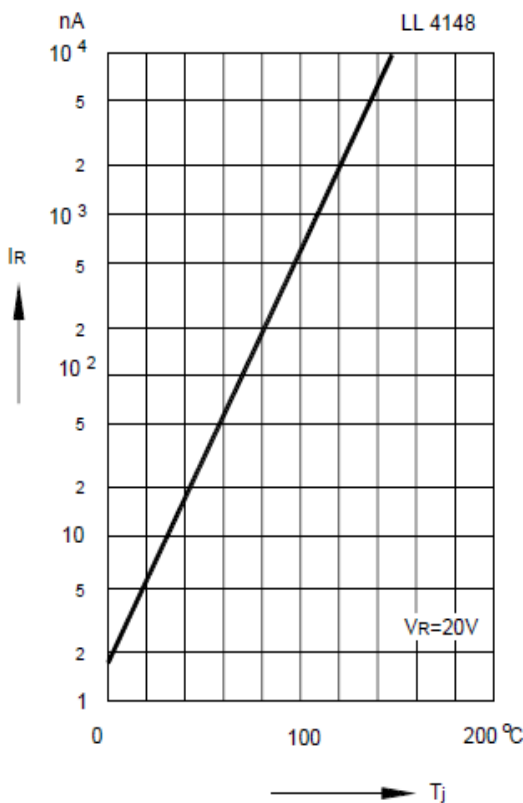
NOTE:(1)Valid provided that electrodes are kept at ambient temperature.



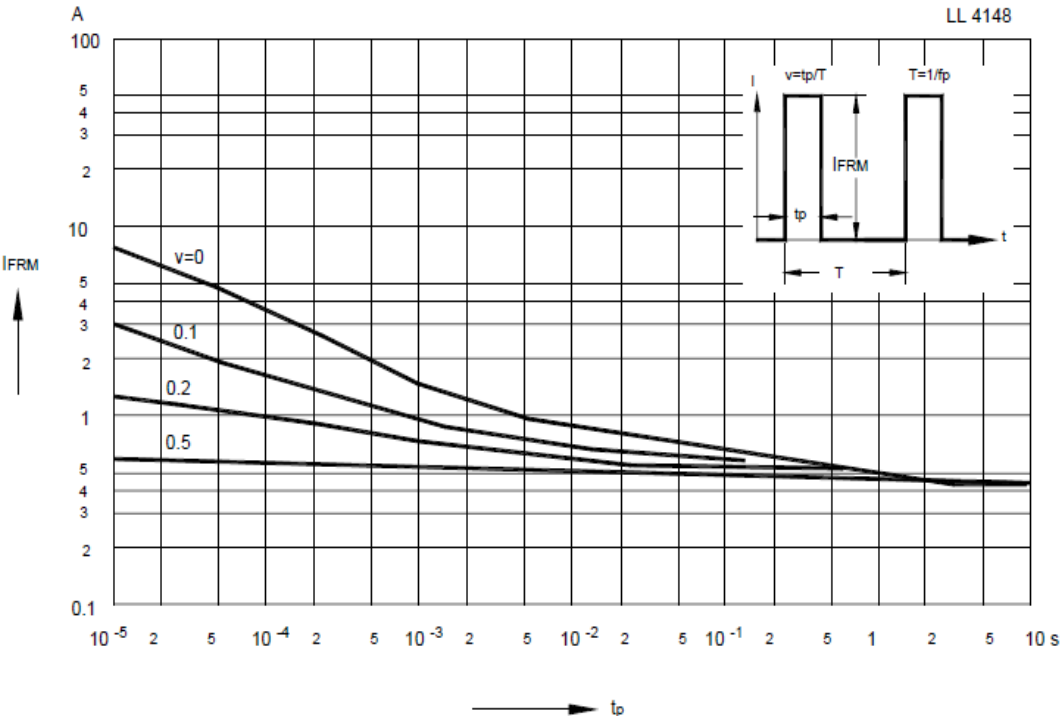
The curve above is for reference only. 曲线图仅供参考。



Leakage current
versus junction temperature



Admissible repetitive peak forward current versus pulse duration
Valid provided that electrodes are kept at ambient temperature



The curve above is for reference only. 曲线图仅供参考。